



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Transistors

2SA1179 TRANSISTOR (PNP)

FEATURES

- High breakdown voltage

MARKING: M

SOT-23



1. BASE
2. EMITTER
3. COLLECTOR

MAXIMUM RATINGS* $T_A=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-55	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-150	mA
P_D	Total Device Dissipation	200	mW
T_J, T_{stg}	Junction and Storage Temperature	-55-125	$^{\circ}\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

ELECTRICAL CHARACTERISTICS($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-55			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-35\text{V}, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-6\text{V}, I_C=-1\text{mA}$	200		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.5	V
Base -emitter saturation voltage	$V_{BE(sat)}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$			-1.0	V
Transition frequency	f_T	$V_{CE}=-6\text{V}, I_C=-10\text{mA}$		180		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-6\text{V}, I_E=0, f=1\text{MHz}$		4		pF